

L-Band RF Power LDMOS Transistor

The high power pulsed transistor part number ILD1214EL100 is designed for L-Band systems operating at 1.215–1.400 GHz. Operating at a pulse width of 16ms with a duty factor of 50%, this dual LDMOS device 100 watts of peak pulse power across the instantaneous operating bandwidth of 1.215-1.400 GHz. Fabricated with all gold metal contact, wire bonding and package for maximum reliability. All devices are 100% screened for large signal RF parameters in the broadband RF test fixture across the entire specified operating bandwidth with no variable or external tuning.



PRELIMINARY BROADBAND DATA

TBD

Silicon LDMOS

- High Power Gain
- Superior Thermal Stability

Class AB Operation

- Gate biased to $I_{DQ}=250\text{mA}$

Configuration

- Common Source

Gold Metal

- Gold Chip Metal
- Gold Wire Bond
- Maximum Reliability

Package

- Thermally Enhanced
- Gold Metal Based

Epoxy Sealed Lid

- Gross Leak Qualified

RF Test Fixture

- Broadband
- Matched to 50Ω
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning required

MAXIMUM RATINGS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Drain-Source Voltage	V_{DS}	--	65	V	--
BD	Gate-Source Voltage	V_{GS}	-0.5	+12	V	--
BD	Storage Temperature Range	T_{STG}	-40	+150	°C	--
BD	Operating Junction Temperature Range	T_J	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

THERMAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	TBD	°C/W	$V_{dd}=30V, I_{DQ}=250mA, T_F=70\pm5^\circ C, P_{OUT}=100W$
Note	Screen 'BD' = parameter qualified By Design.					

PROCESSING SPECIFICATIONS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071, Test Condition C
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

DC ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Drain-Source Breakdown Voltage (each side)	BV_{DSS}	65	--	V	$I_D = 10mA, V_{GS} = 0V, T_F = 25\pm5^\circ C$
BD	Drain Leakage Current (each side)	I_{DSS}	--	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V, T_F = 25\pm5^\circ C$
100%	Gate Threshold Voltage (each side)	V_{GSTH2}	2.0	3.0	V	$I_D = 0.75A, V_{DS} = 30V, T_F = 25\pm5^\circ C$
BD	Gate Leakage Current (each side)	I_{GSS}	--	1.0	μA	$V_{GS} = 10V, V_{DS} = 0V, T_F = 25\pm5^\circ C$

RF ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	RL	-18	-7	dB	$V_{DD}=V1; I_{DQ}=I_{DQ1}; T_F=T_{F1}; P_O=P_{OUT1}; F=F1, F2, F3; PW1, DF1$
100%	Power Gain	G_P	10	16.5	dB	$V_{DD}=V1; I_{DQ}=I_{DQ1}; T_F=T_{F1}; P_O=P_{OUT1}; F=F1, F2, F3; PW1, DF1$
100%	Input Power	P_i	2.24	10.0	W	$V_{DD}=V1; I_{DQ}=I_{DQ1}; T_F=T_{F1}; P_O=P_{OUT1}; F=F1, F2, F3; PW1, DF1$
100%	Drain Current Efficiency	η_D	38	75	%	$V_{DD}=V1; I_{DQ}=I_{DQ1}; T_F=T_{F1}; P_O=P_{OUT1}; F=F1, F2, F3; PW1, DF1$
100%	Pulse Amplitude Droop	Droop	-0.5	0.5	dB	$V_{DD}=V1; I_{DQ}=I_{DQ1}; T_F=T_{F1}; P_O=P_{OUT1}; F=F1, F2, F3; PW1, DF1$
100%	Gain Flatness versus Frequency	GF	0	1.5	dB	$V_{DD}=V1; I_{DQ}=I_{DQ1}; T_F=T_{F1}; P_O=P_{OUT1}; F=F1, F2, F3; PW1, DF1$
100%	Stability into 2:1 VSWR	VSWR-S	2:1	--	--	$V_{DD}=V1; I_{DQ}=I_{DQ1}; T_F=T_{F1}; P_O=P_{OUT1}; F=F1, F2, F3; PW1, DF1$ Rotate 2:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse.
100%	Load Mismatch Tolerance	LMT	TBD	--	--	$V_{DD}=V1; I_{DQ}=I_{DQ1}; T_F=T_{F1}; P_O=P_{OUT1}; F=F1, F2, F3; PW1, DF1$ Rotate output VSWR through 360° phase. Post test $P_O =$ Pre test $P_O \pm 10W$.
Notes	V1=30V; I_{DQ1} (Drain Quiescent Current)=250mA PW1(Pulse Width 1) =16ms; DF1(Duty Factor 1)=50%; P_{OUT1} =100W; F1=1.215GHz, F2=1.300GHz, F3=1.400GHz T_{F1} (Flange Temp)=40±5°C; RF Electrical characteristics are tested in broadband RF test fixture. Thermal grease is applied to the flange for RF testing.					

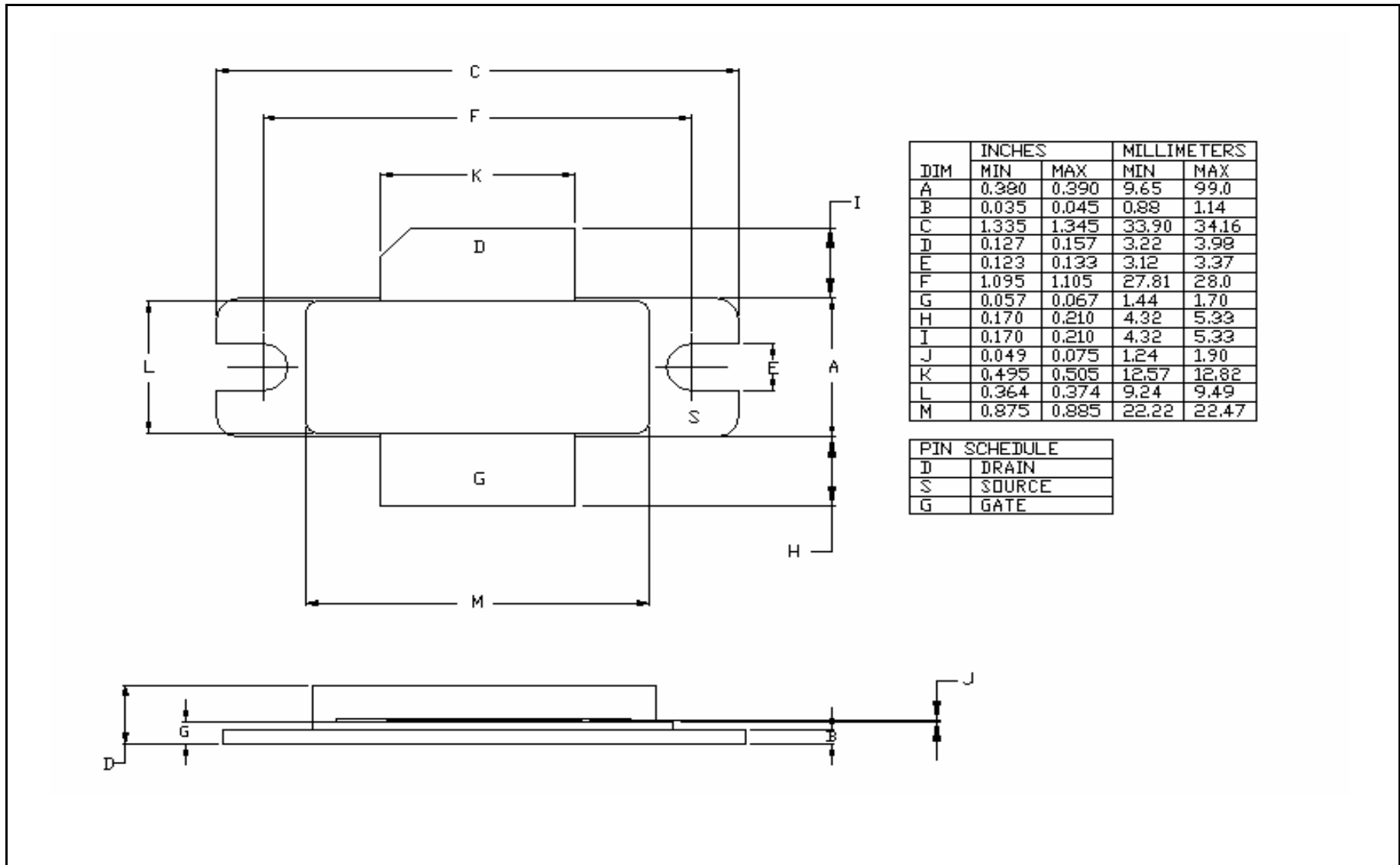
BROADBAND RF TEST FIXTURE IMPEDANCE CHARACTERISTICS

Frequency (GHz)	Z_{IF} (Ω)	Z_{OF} (Ω)
1.215	TBD	TBD
1.300	TBD	TBD
1.400	TBD	TBD

Z_{IF} = The test fixture input impedance.

Z_{OF} = The test fixture output impedance.

PACKAGE DIMENSIONAL OUTLINE DRAWING



RF-TEST-FIXTURE ASSEMBLY AND PART LIST

TBD

RF-TEST-FIXTURE CIRCUIT DIMENSIONS

TBD

RF-TEST-FIXTURE ELECTRICAL SCHEMATIC

TBD

DEFINITIONS

Data Sheet Status	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
Maximum Ratings	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only. Operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

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